

7-27-21

**MPS5172**

**NPN EPITAXIAL SILICON TRANSISTOR**

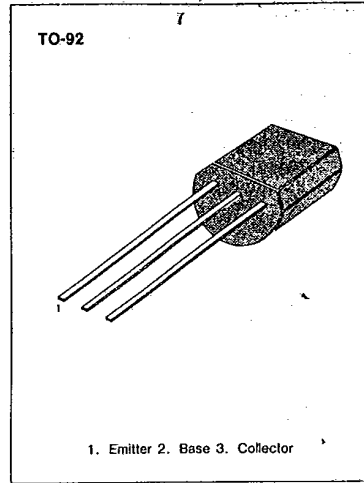
**AMPLIFIER TRANSISTOR**

- Collector-Emitter Voltage:  $V_{CE0} = 25V$
- Collector Dissipation:  $P_C (max) = 625mW$

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	25	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	100	mA
Collector Dissipation	$P_C$	625	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 - 150	$^\circ C$

• Refer to MPSA10 for graphs



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**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C = 10mA, I_B = 0$	25			V
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 25V, I_E = 0$			100	nA
Collector Cut-off Current	$I_{CES}$	$V_{CE} = 25V, V_{BE} = 0$			100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{BE} = 5V, I_C = 0$			100	nA
*DC Current Gain	$h_{FE}$	$I_C = 10mA, V_{CE} = 10V$	100		500	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$			0.25	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10mA, I_B = 1mA$		0.75		V
Current Gain Bandwidth Product	$f_T$	$I_C = 2mA, V_{CE} = 5V$		120		MHz
Base Emitter On Voltage	$V_{BE(on)}$	$I_C = 10mA, V_{CE} = 10V$	0.5		1.2	V

\* Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$